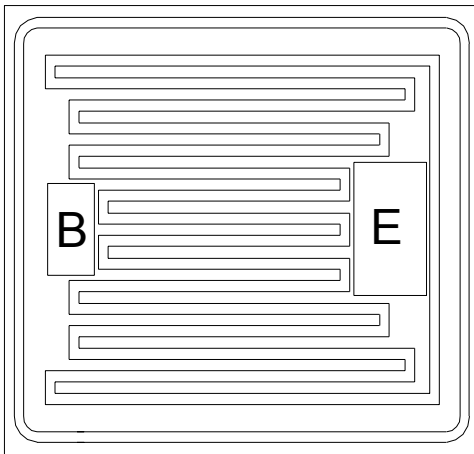


PROCESS DETAILS

| | |
|--------------------------|----------------------------------|
| PROCESS | EPITAXIAL BASE |
| DIE SIZE | 80 x 80 MILS |
| DIE THICKNESS | 12 MILS |
| BASE BONDING PAD AREA | 12 x 18 MILS |
| EMITTER BONDING PAD AREA | 13 x 28 MILS |
| TOP SIDE METALIZATION | Al - 30,000Å |
| BACK SIDE METALIZATION | Cr/Ni/Ag - Ni-6,000Å; Ag-10,000Å |

GEOMETRY



BACKSIDE COLLECTOR

PRINCIPAL DEVICE TYPES

CJD41C
TIP41C

Please refer to
selection guide on page 20.